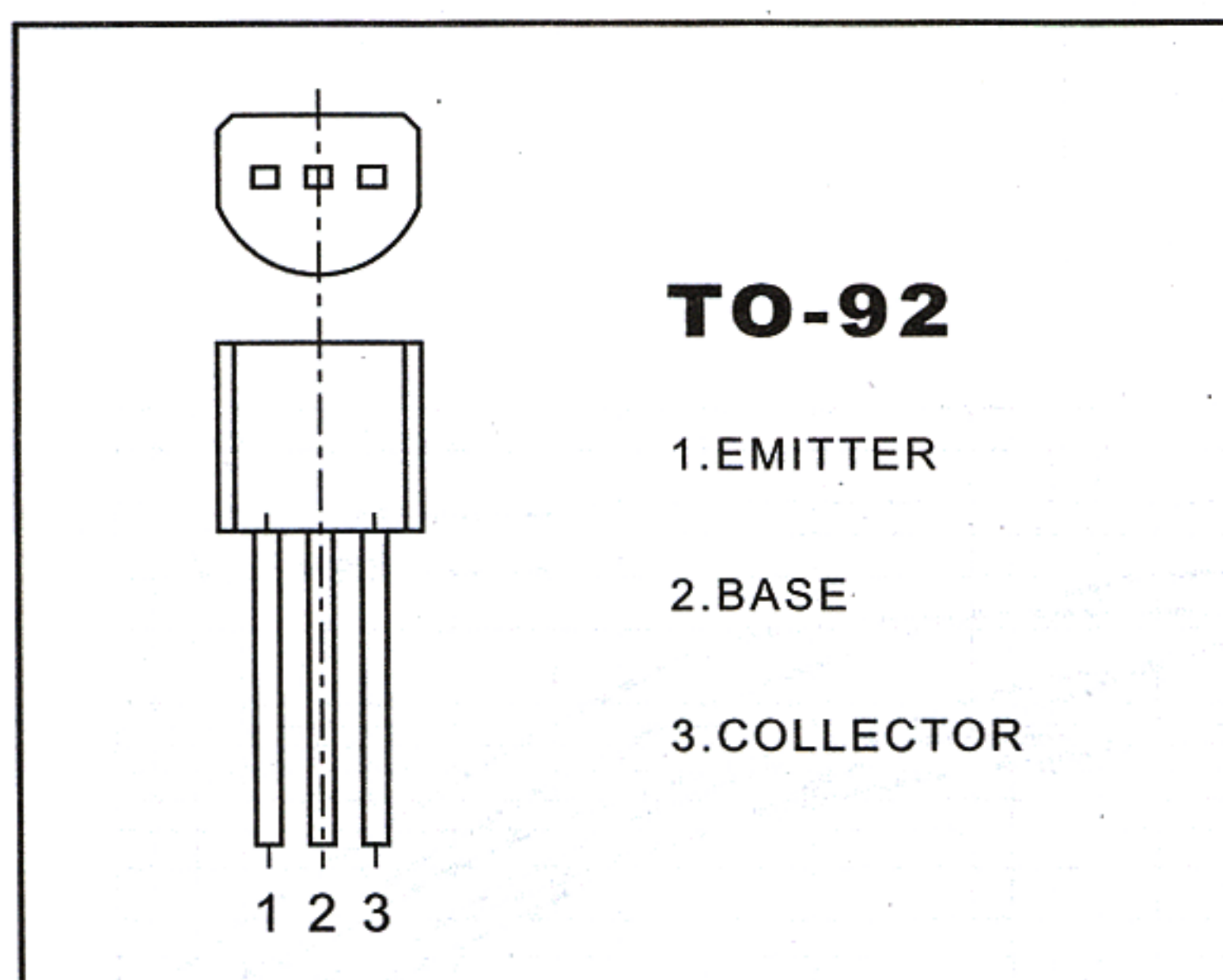


TO-92 Plastic-Encapsulate Transistors

2N5551 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.625W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 180V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

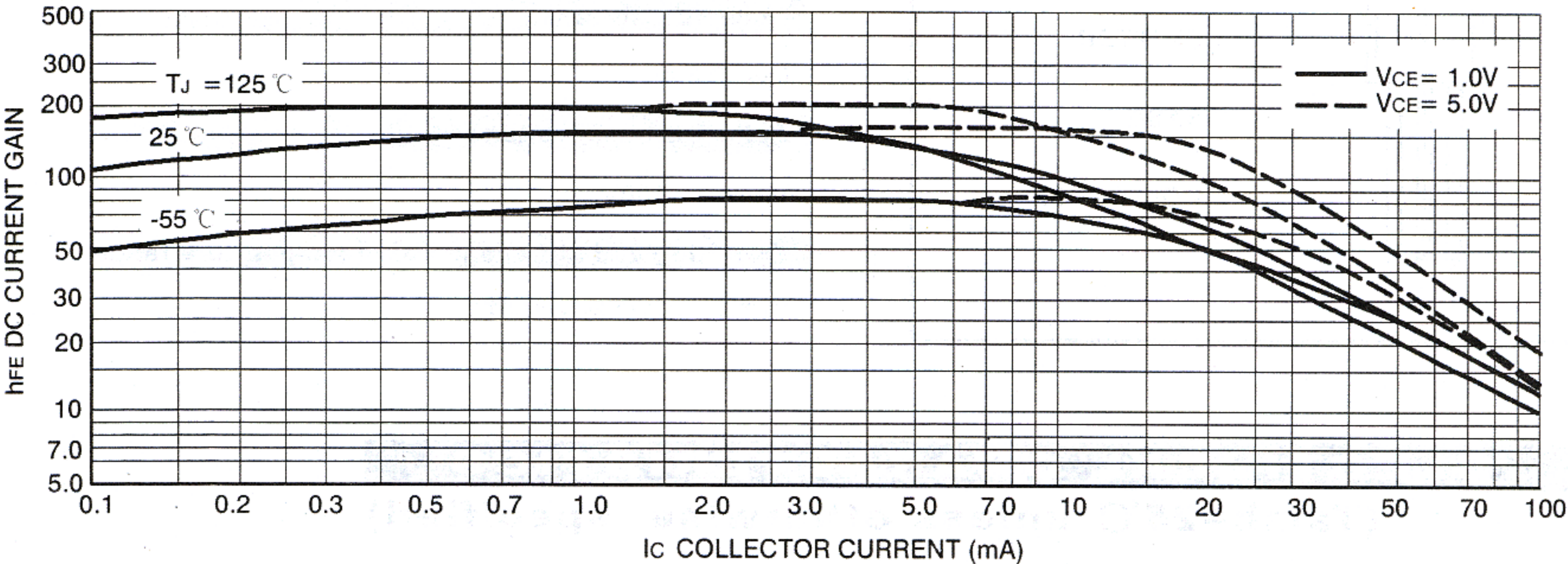
ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

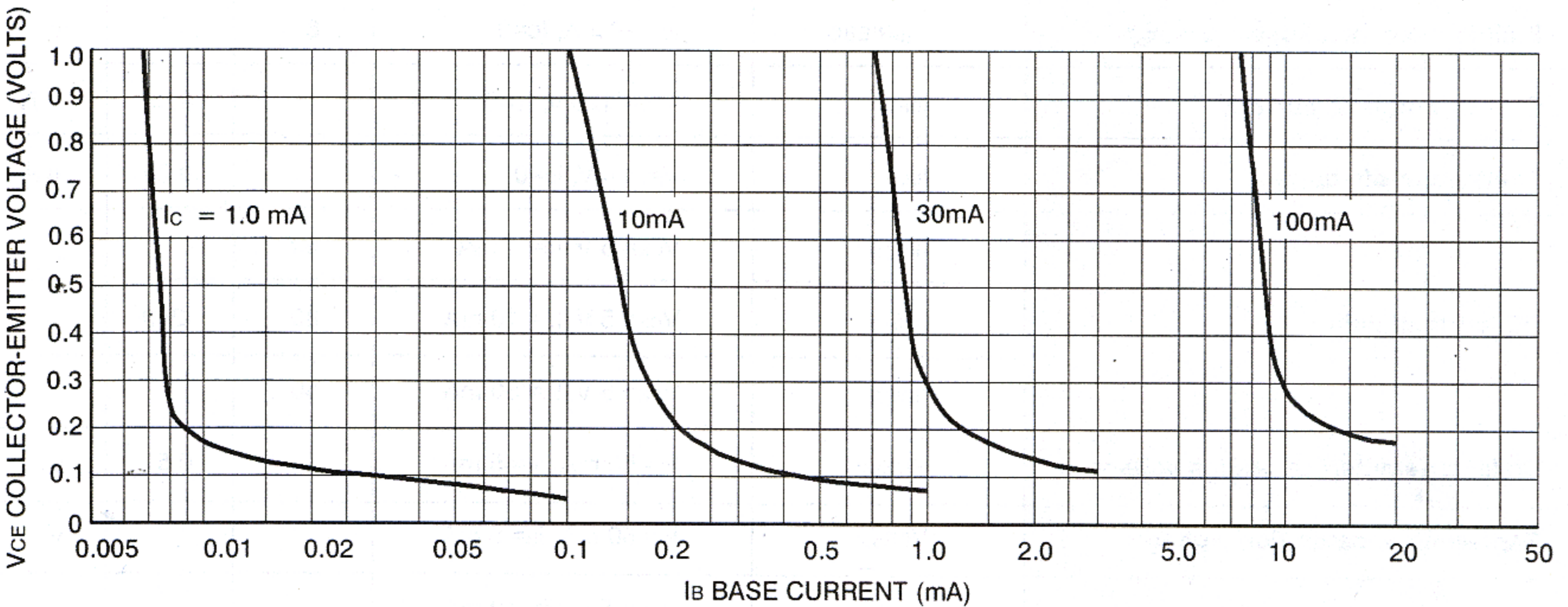
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	180		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 mA, I_B = 0$	160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10 \mu A, I_C = 0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB} = 120 V, I_E = 0$		0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 V, I_C = 0$		0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 5 V, I_C = 1 mA$	80		
	$h_{FE(2)}$	$V_{CE} = 5 V, I_C = 10 mA$	80	250	
	$h_{FE(3)}$	$V_{CE} = 5 V, I_C = 50 mA$	50		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 50 mA, I_B = 5 mA$		0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 50 mA, I_B = 5 mA$		1	V
Transition frequency	f_T	$V_{CE} = 5 V, I_C = 10 mA$ $f = 30 MHz$	100		MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B	C
Range	80-160	120-180	150-250



DC Current Gain



Collector Saturation Region